

Features

- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS Tested
- 100% ΔV_{ds} Tested
- Halogen-free; RoHS-compliant

Applications

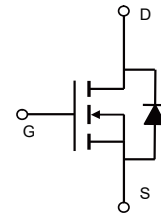
- SMPS with PFC,
- Flyback and LLC topologies
- Silver ATX, adapter, TV, lighting, Telecom

Product Summary

Parameters	Value	Unit
V_{DSS}	650	V
$V_{GS(th)}_{Typ}$	3.8	V
$I_D(@V_{GS}=10V)$	22	A
$R_{DS(ON)}_{Typ}(@V_{GS}=10V)$	70	m Ω



TO-3PN



Schematic

Ordering Information

Device	Marking	MSL	Form	Package	Tube(pcs)	Per Carton (pcs)
VSM22N65-TPN	VSM22N65	N/A	Tube	TO-3PN	30	2250

Absolute Maximum Ratings (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-to-Source Voltage	650	V
V_{GS}	Gate-to-Source Voltage	± 30	V
I_D	Continuous Drain Current	$T_A = 25^\circ\text{C}$	A
		$T_A = 100^\circ\text{C}$	
I_{DM}	Pulsed Drain Current ⁽¹⁾	Refer to Fig.4	A
E_{AS}	Single Pulsed Avalanche Energy ⁽²⁾	304	mJ
P_D	Power Dissipation	$T_A = 25^\circ\text{C}$	W
		$T_A = 100^\circ\text{C}$	
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽³⁾	33	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽⁴⁾	1.3	

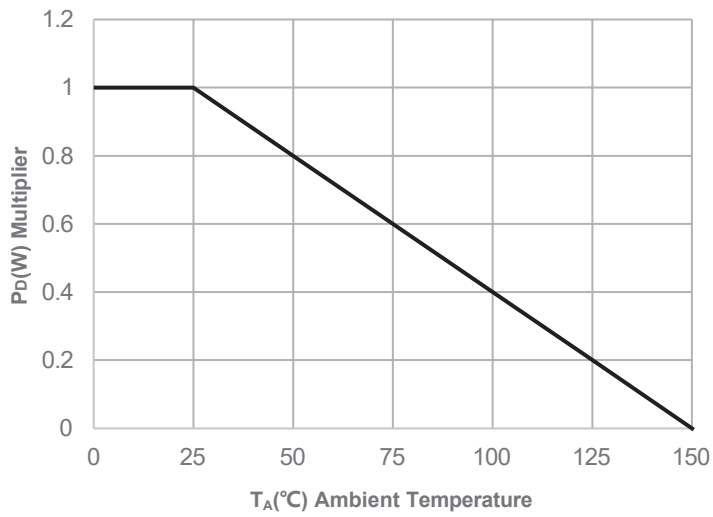
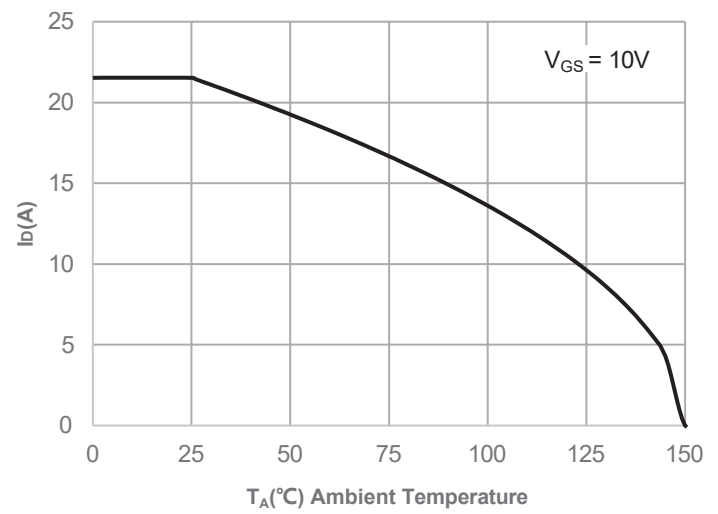
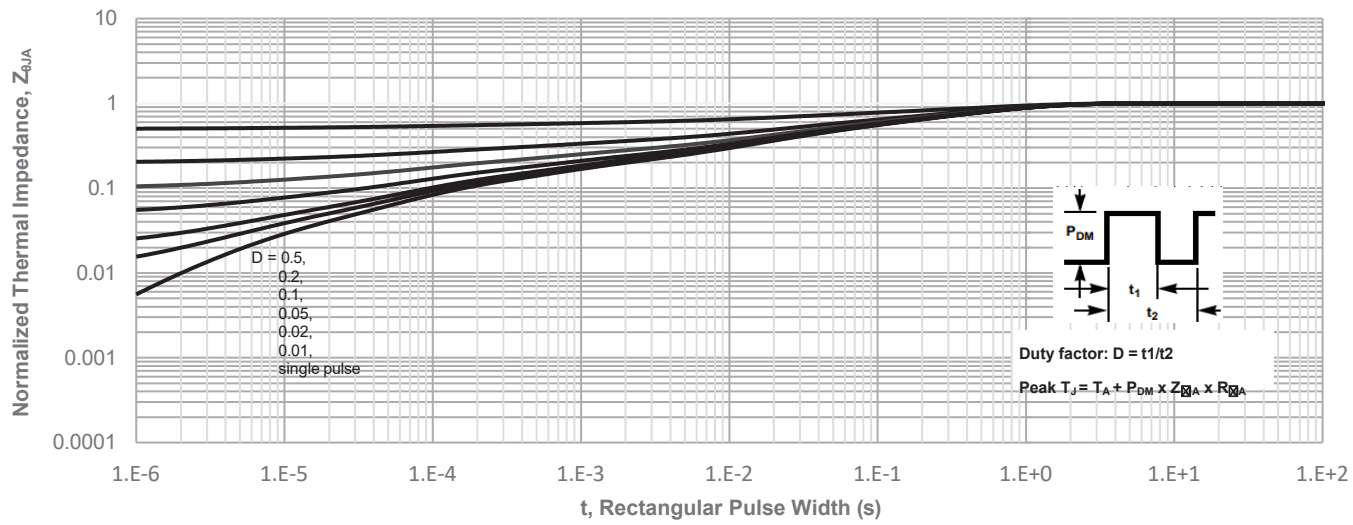
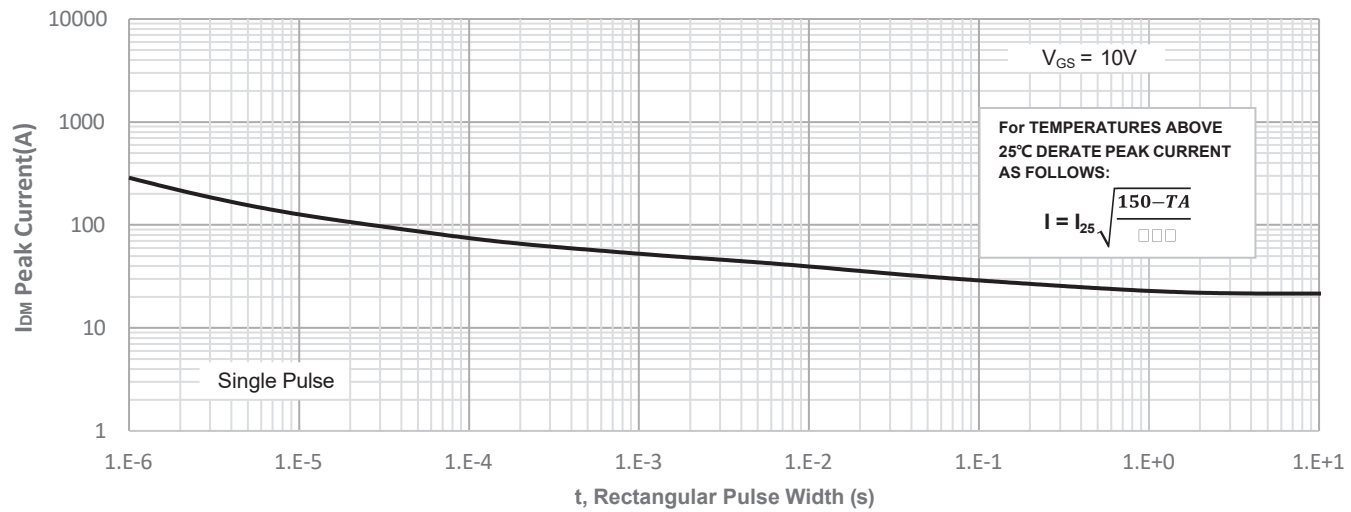
Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0V	650	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 650V, V _{GS} = 0V	-	-	20.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{DS} = 0V, V _{GS} = ±30V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	2.7	3.8	5.0	V
R _{DS(ON)}	Static Drain-Source ON-Resistance ⁽⁵⁾	V _{GS} = 10V, I _D = 20A	-	70	90	mΩ
Dynamic Characteristics						
R _g	Gate Resistance	f = 1MHz	-	3.3	-	Ω
C _{iss}	Input Capacitance	V _{GS} = 0V, V _{DS} = 325V, f = 1MHz	1995	2793	3771	pF
C _{oss}	Output Capacitance		46	64	86	pF
C _{rss}	Reverse Transfer Capacitance		-	6.8	-	pF
Q _g	Total Gate Charge	V _{GS} = 0 to 10V V _{DS} = 325V, I _D = 20A	41	58	78	nC
Q _{gs}	Gate Source Charge		15	20	27	nC
Q _{gd}	Gate Drain("Miller") Charge		16	22	29	nC
Switching Characteristics						
t _{d(on)}	Turn-On DelayTime	V _{GS} = 10V, V _{DD} = 330V I _D = 20A, R _{GEN} = 24 Ω	-	66	-	ns
t _r	Turn-On Rise Time		-	67	-	ns
t _{d(off)}	Turn-Off DelayTime		-	155	-	ns
t _f	Turn-Off Fall Time		-	45	-	ns
Body Diode Characteristics						
I _S	Maximum Continuous Body Diode Forward Current		-	-	22	A
I _{SM}	Maximum Pulsed Body Diode Forward Current		-	-	88	A
V _{SD}	Body Diode Forward Voltage	V _{GS} = 0V, I _S = 20A	-		1.2	V
t _{rr}	Body Diode Reverse Recovery Time	I _F = 20A, di/dt = 100A/us	137	192	259	ns
Q _{rr}	Body Diode Reverse Recovery Charge		-	1230	-	nC

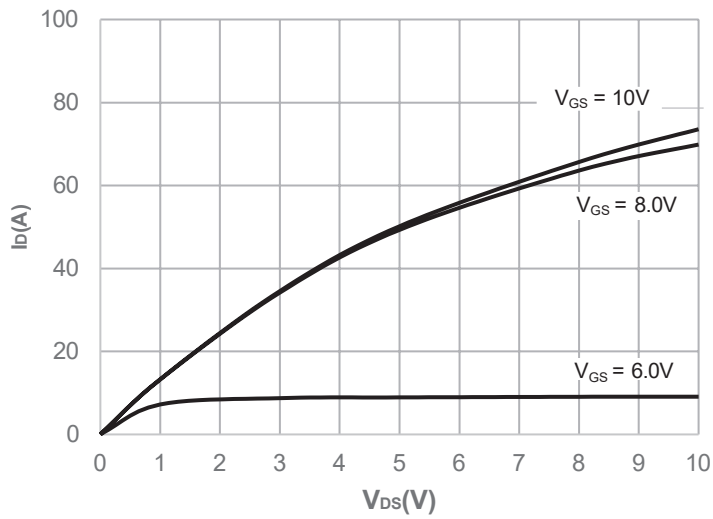
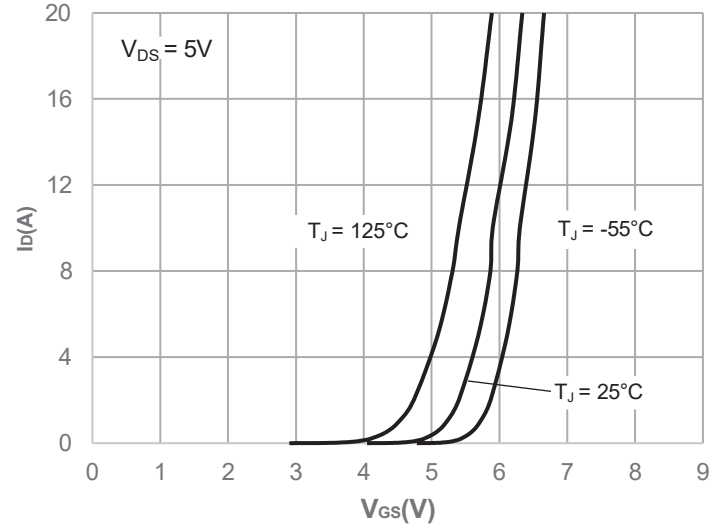
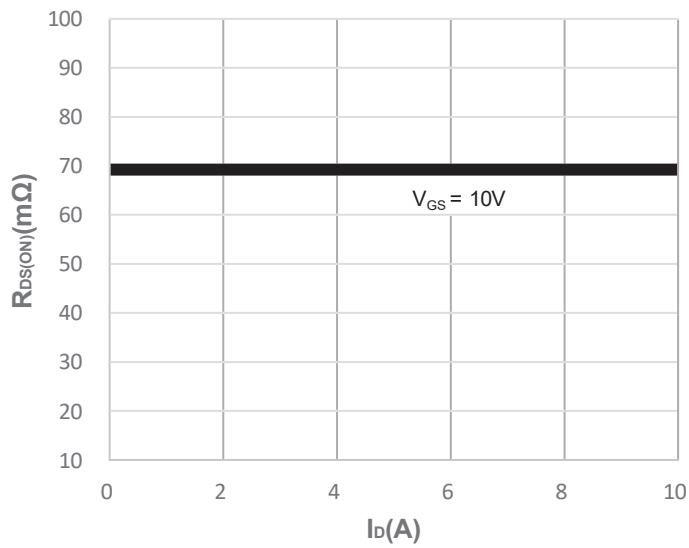
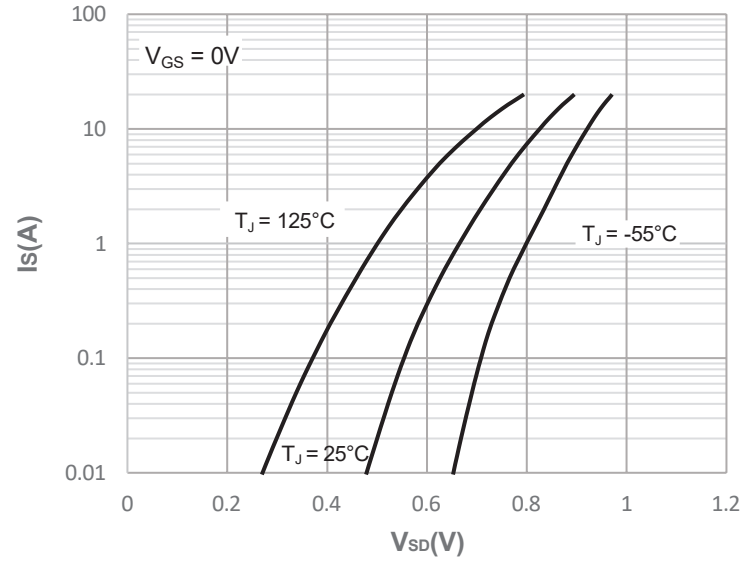
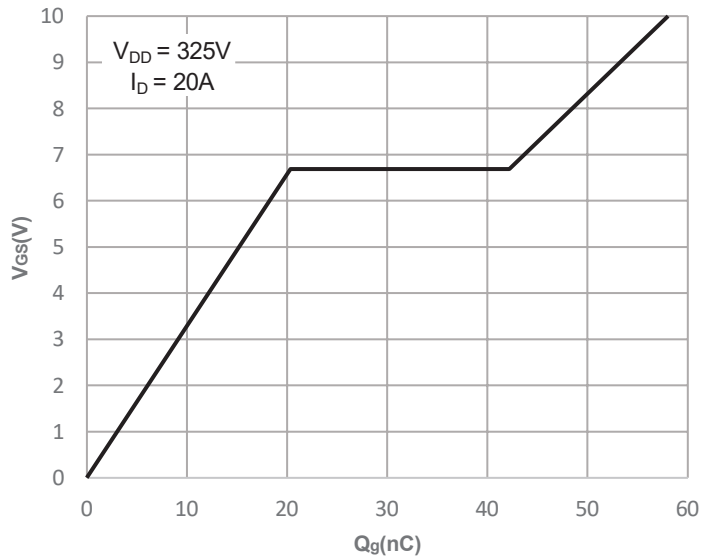
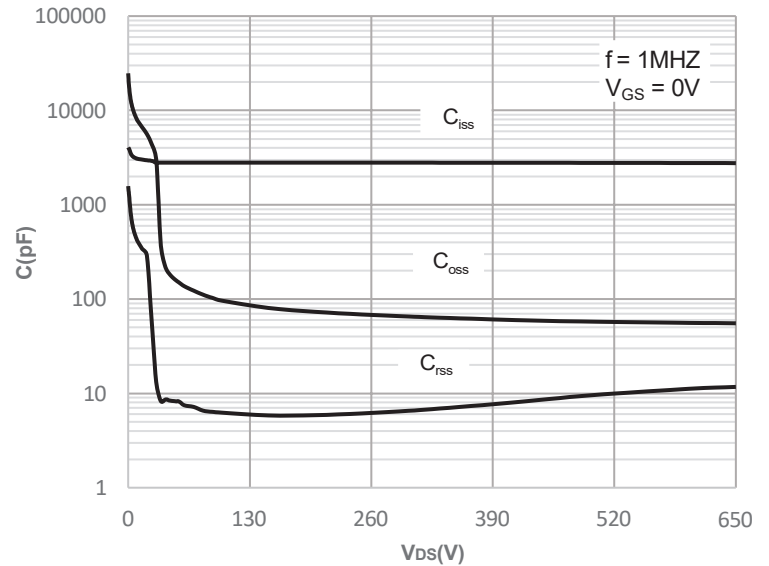
Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. E_{AS} condition: Starting $T_J=25^\circ\text{C}$, $V_{DD}=325\text{V}$, $V_{GS}=10\text{V}$, $R_G=25\text{ohm}$, $L=10\text{mH}$, $I_{AS}=7.8\text{A}$, $V_{DD}=0\text{V}$ during time in avalanche.
3. $R_{\theta JA}$ is measured with the device mounted on a minimum recommended pad of 2oz copper FR4 PCB.
4. $R_{\theta JA}$ is measured with the device mounted on a 1inch² pad of 2oz copper FR4 PCB.
5. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.

Typical Performance Characteristics

Figure 1: Power De-rating

Figure 2: Current De-rating

Figure 3: Normalized Maximum Transient Thermal Impedance

Figure 4: Peak Current Capacity


Typical Performance Characteristics

Figure 5: Output Characteristics

Figure 6: Typical Transfer Characteristics

Figure 7: On-resistance vs. Drain Current

Figure 8: Body Diode Characteristics

Figure 9: Gate Charge Characteristics

Figure 10: Capacitance Characteristics


Typical Performance Characteristics

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

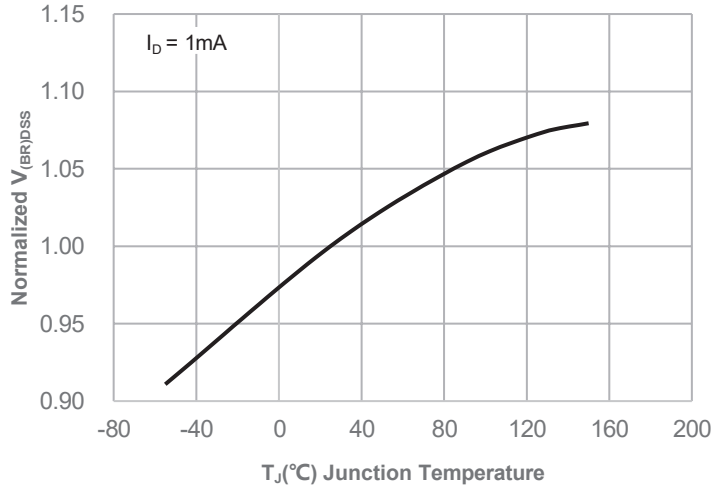


Figure 12: Normalized on Resistance vs. Junction Temperature

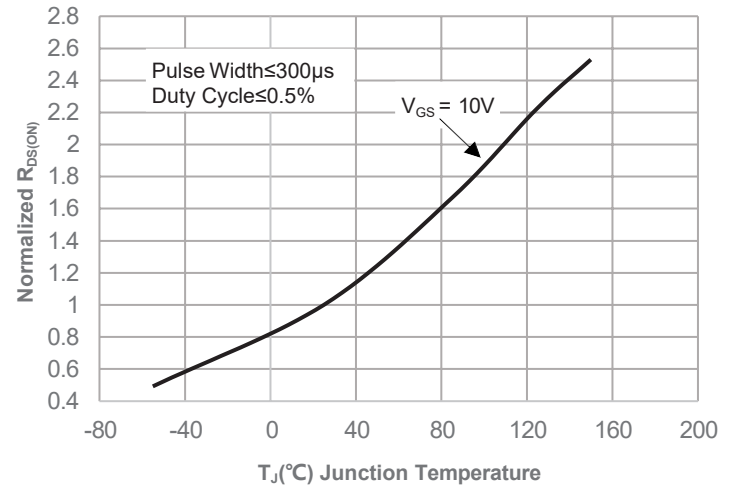


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

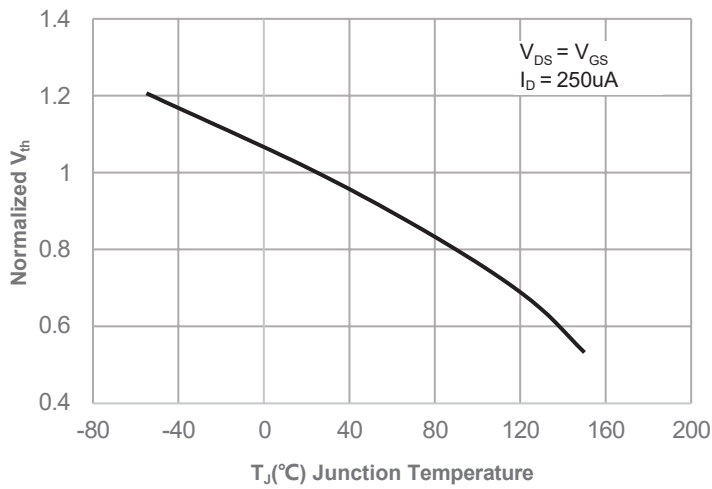


Figure 14: $R_{DS(ON)}$ vs. V_{GS}

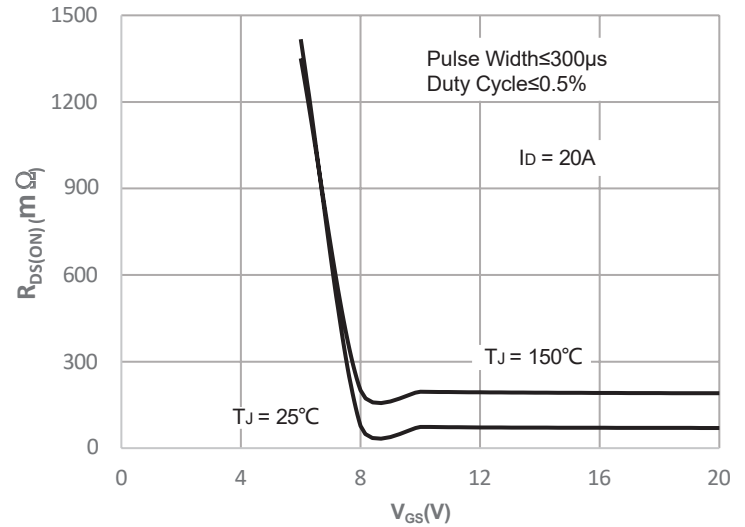
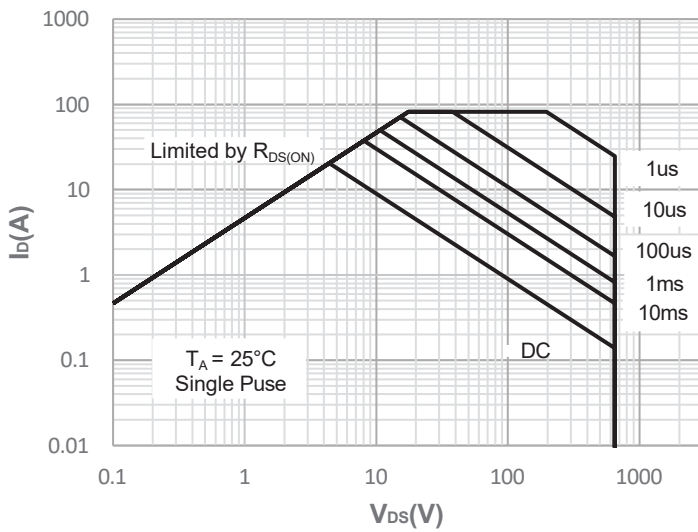


Figure 15: Maximum Safe Operating Area



Test Circuit



Figure 1: Gate Charge Test Circuit & Waveform

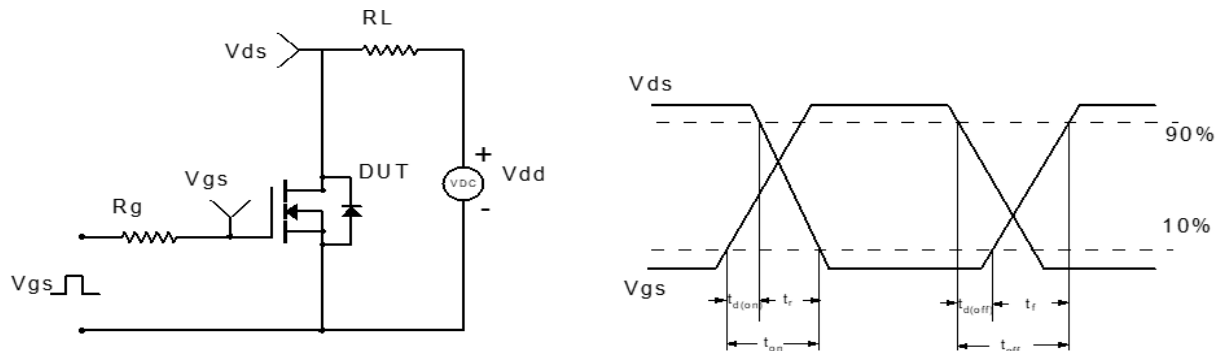


Figure 2: Resistive Switching Test Circuit & Waveform

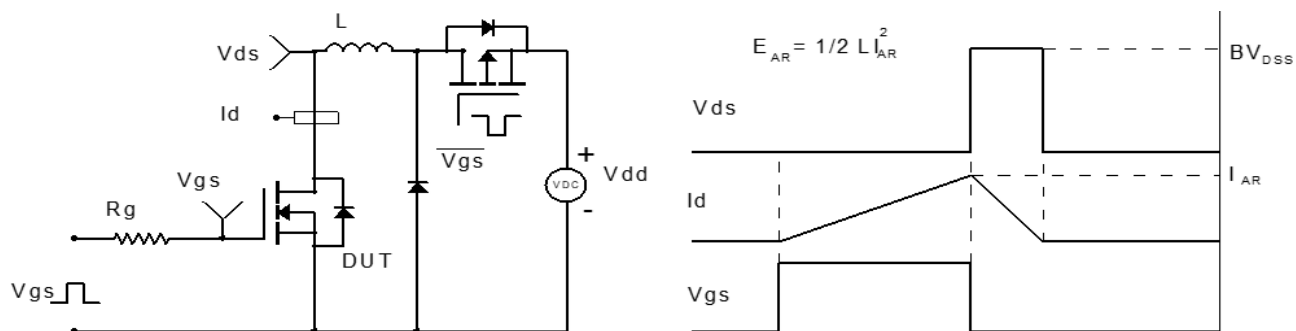


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

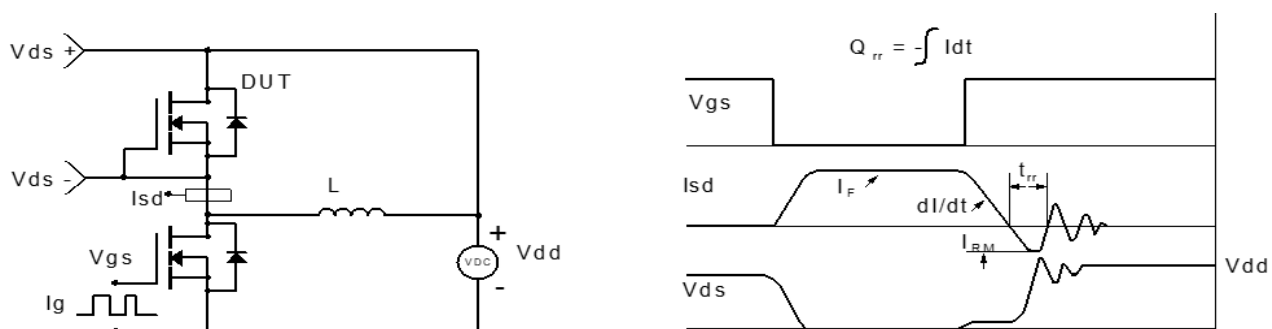


Figure 4: Diode Recovery Test Circuit & Waveform